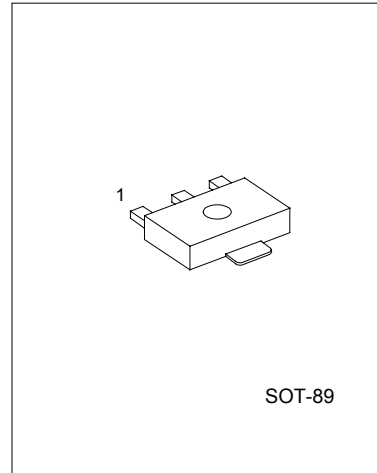


UTC2SD1898 NPN EPITAXIAL SILICON TRANSISTOR

POWER TRANSISTOR

FEATURES

- *High $V_{CE0} = 80V$
- *High $I_c = 1A$ (DC)
- *Good h_{FE} linearity.
- *Low $V_{CE(sat)}$
- *Complements the 2SB1260.



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current(DC)	I_c	1	A
Collector Current(PULSE)*1	I_{cp}	2	A
Collector Power Dissipation*2	P_c	0.5	W
Collector Power Dissipation*2	P_c	2	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}C$

*1 Duty=1/2, $P_w=200ms$

*2 When mounted on a 40*40*0.7 mm ceramic board.

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	$I_c = 50 \mu A$	100			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_c = 1mA$	80			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = 50 \mu A$	5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 80V, I_E = 0A$			1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 4V, I_C = 0A$			1	μA
DC Current Transfer Ratio	h_{FE}	$V_{CE} = 3V, I_c = 0.5A$	82		390	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 500mA, I_B = 20mA$		0.15	0.4	V
Transition Frequency	f_T	$V_{CE} = 10V, I_E = -50 mA, f = 100MHz$		100		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0 A, f = 1MHz$		20		pF

CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390

UTC2SD1898 NPN EPITAXIAL SILICON TRANSISTOR

ELECTRICAL CHARACTERISTICS CURVES

Figure 1. Grounded Emitter Propagation Characteristics

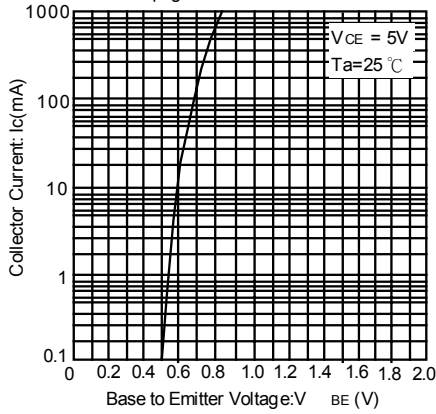


Figure 2. Grounded Emitter Output Characteristics

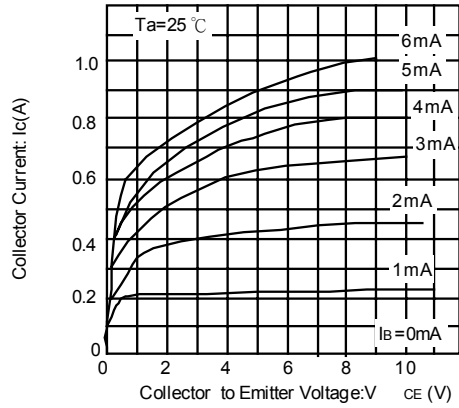


Figure 3. DC Current Gain vs. Collector Current

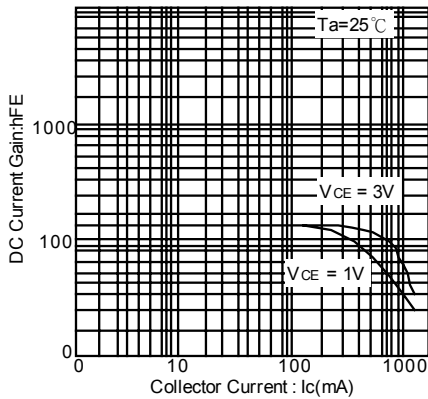


Figure 4. Collector-emitter Saturation Voltage vs. Collector Current

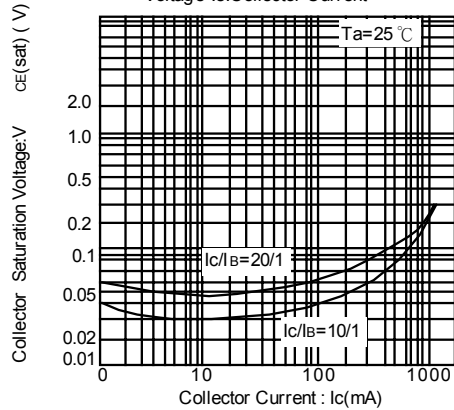


Figure 5. Gain Bandwidth Product vs. Emitter Current

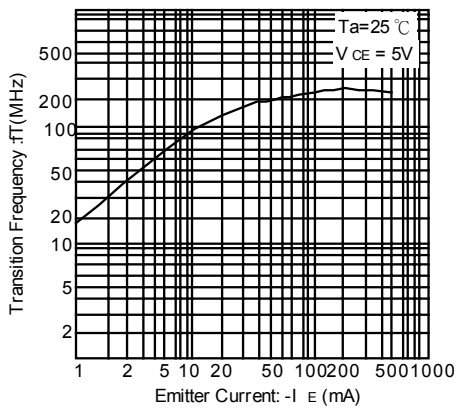
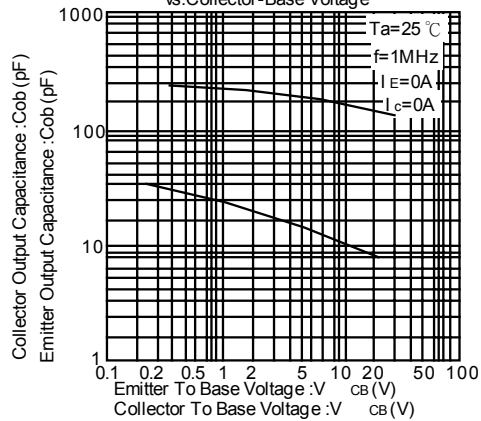
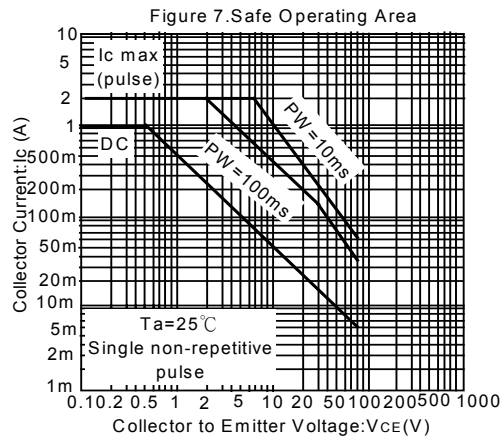


Figure 6. Collector Output Capacitance vs. Collector-Base Voltage



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